

TLE2061, TLE2061A, TLE2061B, TLE2061Y
EXCALIBUR JFET-INPUT HIGH-OUTPUT-DRIVE
 μ POWER OPERATIONAL AMPLIFIERS
SLOS045F – OCTOBER 1989 – REVISED SEPTEMBER 1996

- **Excellent Output Drive Capability**
 $V_O = \pm 2.5 \text{ V Min at } R_L = 100 \, \Omega$,
 $V_{CC\pm} = \pm 5 \text{ V}$
 $V_O = \pm 12.5 \text{ V Min at } R_L = 600 \, \Omega$,
 $V_{CC} = \pm 15 \text{ V}$
- **Low Supply Current** . . . 280 $\mu\text{A Typ}$
- **High Unity-Gain Bandwidth**
1.8 MHz Typ
- **High Slew Rate** . . . 3.4 V/ $\mu\text{s Typ}$
- **Macromodels Included**
- **Wide Operating Supply Voltage Range**
 $V_{CC\pm} = \pm 3.5 \text{ V to } \pm 19 \text{ V}$
- **High Open-Loop Gain** . . . 230 V/mV Typ
- **Low Offset Voltage** . . . 500 $\mu\text{V Max}$
- **Low Offset Voltage Drift With Time**
0.04 $\mu\text{V/mo Typ}$
- **Low Input Bias Current** . . . 4 pA Typ

description

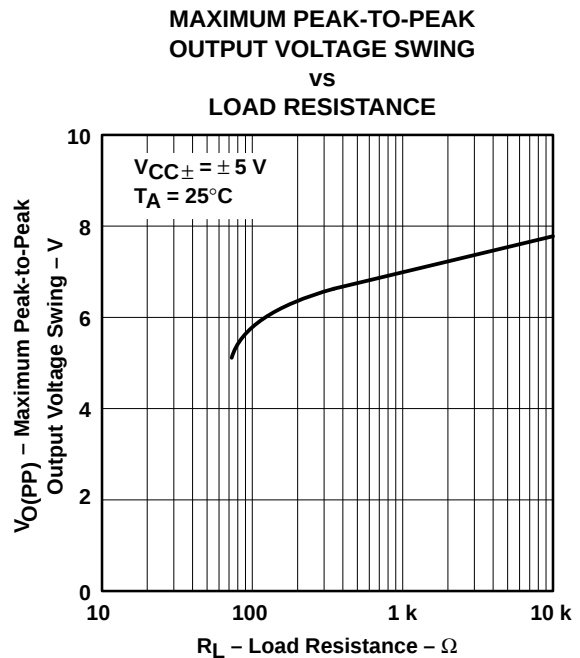
The TLE2061, TLE2061A, TLE2061B, and TLE2061Y are JFET-input, low-power, precision operational amplifiers manufactured using Texas Instruments Excalibur process. These devices combine outstanding output drive capability with low power consumption, excellent dc precision, and wide bandwidth.

In addition to maintaining the traditional JFET advantages of fast slew rates and low input bias and offset currents, the Excalibur process offers outstanding parametric stability over time and temperature. This results in a precision device remaining precise even with changes in temperature and over years of use.

The TLE2061, TLE2061A, and TLE2061B are ideal choices for any application requiring excellent dc precision, high output drive, wide bandwidth, and low power consumption.

A variety of available package options includes small-outline (D) and chip-carrier (FK) versions for high-density system applications.

The C-suffix devices are characterized for operation from 0°C to 70°C. The I-suffix devices are characterized for operation from -40°C to 85°C. The M-suffix devices are characterized for operation over the full military temperature range of -55°C to 125°C.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

**TEXAS
INSTRUMENTS**

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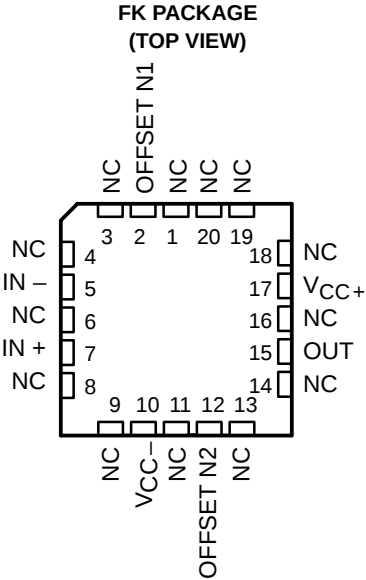
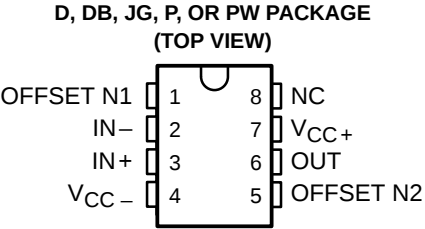
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AVAILABLE OPTIONS

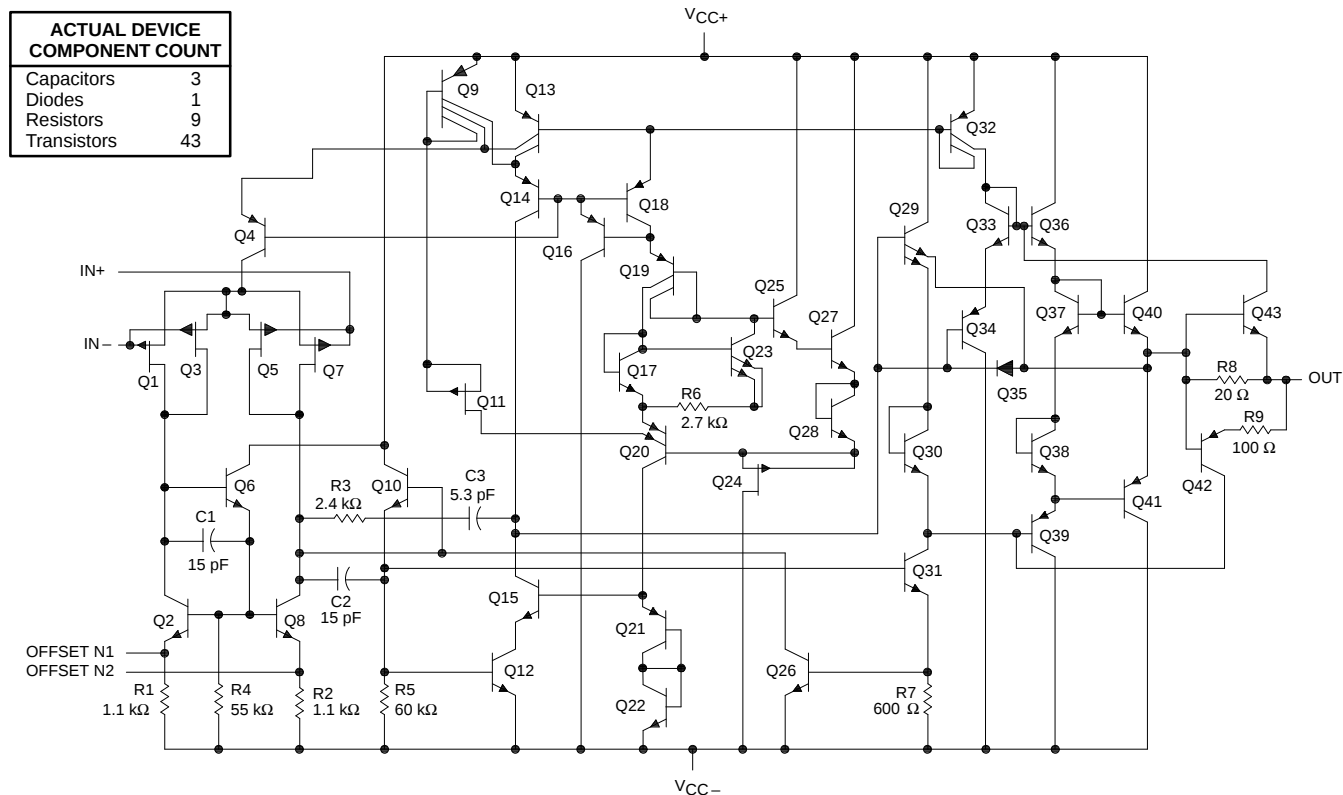
PACKAGED DEVICES								CHIP FORM (Y)
T _A	V _{IO} max AT 25°C	SMALL OUTLINE (D)	SSOP (DB)	CHIP CARRIER (FK)	CERAMIC DIP (JG)	PLASTIC DIP (P)	TSSOP (PW)	
0°C to 70°C	500 μV	—	—	—	—	—	—	TLE2061Y
	1.5 mV	TLE2061ACD	—	—	—	TLE2061ACP	—	
	3 mV	TLE2061CD	TLE2061CDBLE	—	—	TLE2061CP	TLE2061CPWLE	
–40°C to 85°C	500 μV	—	—	—	—	—	—	—
	1.5 mV	TLE2061AID	—	—	—	TLE2061AIP	—	
	3 mV	TLE2061ID	—	—	—	TLE2061IP	—	
–55°C to 125°C	500 μV	—	—	—	—	—	—	—
	1.5 mV	TLE2061AMD	—	TLE2061AMFK	TLE2061AMJG	TLE2061AMP	—	
	3 mV	TLE2061MD	—	TLE2061MFK	TLE2061MJG	TLE2061MP	—	

The D packages are available taped and reeled. Add R suffix to device type (e.g., TLE2061ACDR). The DB and PW packages are available left-end taped and reeled (indicated by the LE suffix on the device type (e.g., TLE2061CDBLE). Chips are tested at 25°C.



NC – No internal connection

equivalent schematic



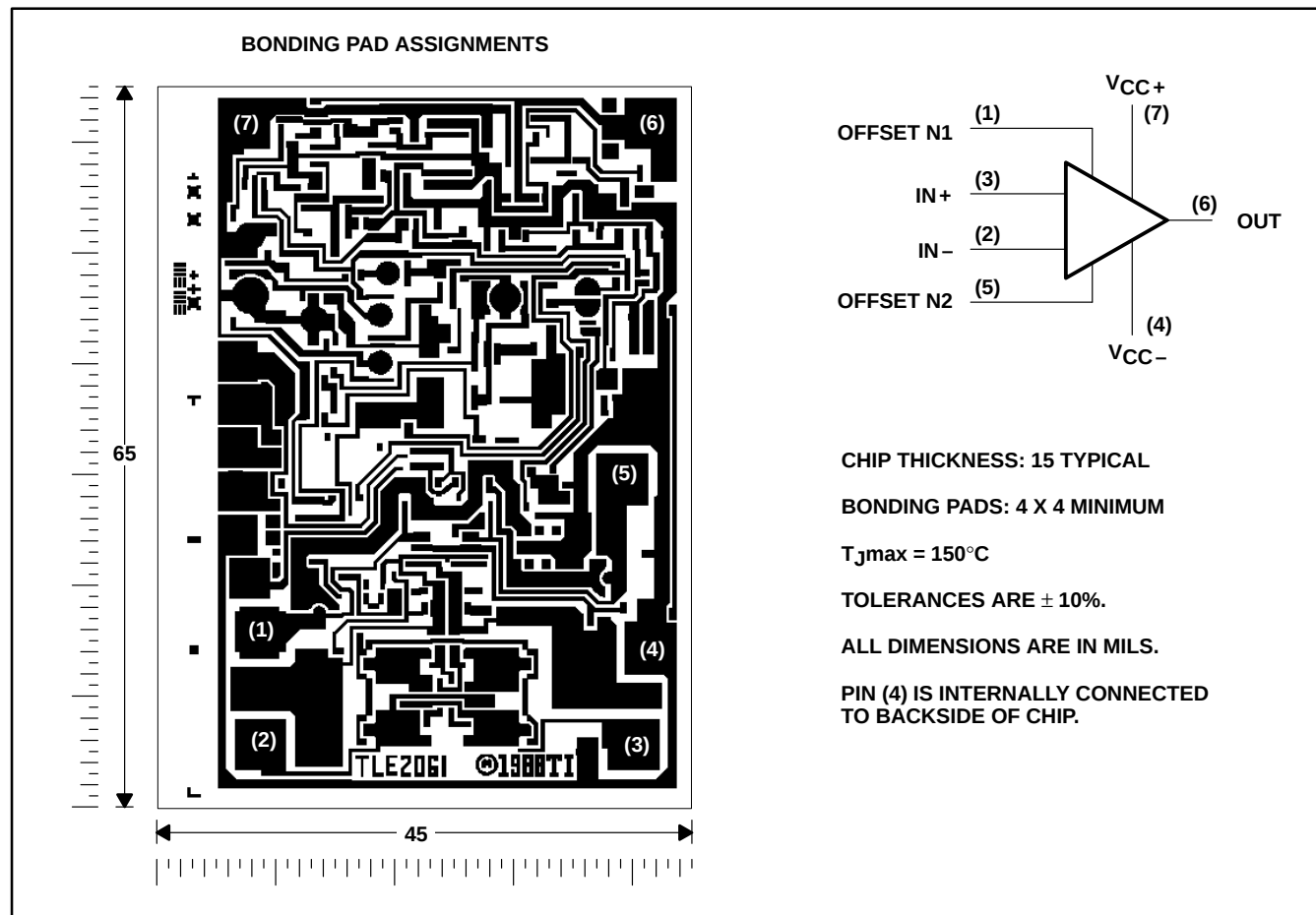
All component values are nominal.

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TLE2061Y chip information

This chip, when properly assembled, displays characteristics similar to the TLE2061. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. Chips may be mounted with conductive epoxy or a gold-silicon preform.



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Supply voltage, V_{CC+} (see Note 1)	19 V
Supply voltage, V_{CC-}	–19 V
Differential input voltage, V_{ID} (see Note 2)	±38 V
Input voltage range, V_I (any input)	± V_{CC}
Input current, I_I (each input)	±1 mA
Output current, I_O	±80 mA
Total current into V_{CC+}	80 mA
Total current out of V_{CC-}	–80 mA
Duration of short-circuit current at (or below) 25°C (see Note 3)	unlimited
Continuous total dissipation	See Dissipation Rating Table
Operating free-air temperature range, T_A : C suffix	0°C to 70°C
I suffix	–40°C to 85°C
M suffix	–55°C to 125°C
Storage temperature range	–65°C to 150°C
Case temperature for 60 seconds: FK package	260°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds: D, DB, P, or PW package	260°C
Lead temperature 1,6 mm (1/16 inch) from case for 60 seconds: JG package	300°C

[†] Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values, except differential voltages, are with respect to the midpoint between V_{CC+} and V_{CC-} .
 2. Differential voltages are at $IN+$ with respect to $IN-$.
 3. The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure that the maximum dissipation rating is not exceeded.

DISSIPATION RATING TABLE

PACKAGE	$T_A \leq 25^\circ\text{C}$ POWER RATING	DERATING FACTOR ABOVE $T_A = 25^\circ\text{C}$	$T_A = 70^\circ\text{C}$ POWER RATING	$T_A = 85^\circ\text{C}$ POWER RATING	$T_A = 125^\circ\text{C}$ POWER RATING
D	725 mW	5.8 mW/°C	464 mW	377 mW	145 mW
DB	525 mW	4.2 mW/°C	336 mW	—	—
FK	1375 mW	11.0 mW/°C	880 mW	715 mW	275 mW
JG	1050 mW	8.4 mW/°C	672 mW	546 mW	210 mW
P	1000 mW	8.0 mW/°C	640 mW	520 mW	200 mW
PW	525 mW	4.2 mW/°C	336 mW	—	—

recommended operating conditions

		C SUFFIX		I SUFFIX		M SUFFIX		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
Supply voltage, $V_{CC\pm}$		±3.5	±18	±3.5	±18	±3.5	±18	V
Common-mode input voltage, V_{IC}	$V_{CC\pm} = \pm 5\text{ V}$	–1.6	4	–1.6	4	–1.6	4	V
	$V_{CC\pm} = \pm 15\text{ V}$	–11	13	–11	13	–11	13	
Operating free-air temperature, T_A		0	70	–40	85	–55	125	°C

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electrical characteristics at specified free-air temperature, $V_{CC\pm} = \pm 5$ V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T _A [†]	TLE2061C TLE2061AC TLE2061BC			UNIT
				MIN	TYP	MAX	
V _{IO}	Input offset voltage	V _{IC} = 0, R _S = 50 Ω	25°C	0.8	3.1	mV	
			Full range	4			
			25°C	0.6	2.6		
			Full range	3.5			
			25°C	0.5	1.9		
			Full range	2.4			
α _{VIO}	Temperature coefficient of input offset voltage		Full range	6		μV/°C	
Input offset voltage long-term drift (see Note 4)			25°C	0.04		μV/mo	
I _{IO}	Input offset current		25°C	1		pA	
			Full range	0.8		nA	
			25°C	3		pA	
I _{IB}			Full range	2		nA	
V _{ICR}	Common-mode input voltage range	25°C	−1.6 to 4	−2 to 6	V		
		Full range	−1.6 to 4		V		
V _{OM+}	Maximum positive peak output voltage swing	R _L = 10 kΩ	25°C	3.5	3.7	V	
			Full range	3.3			
		R _L = 100 Ω	25°C	2.5	3.1		
			Full range	2			
V _{OM−}	Maximum negative peak output voltage swing	R _L = 10 kΩ	25°C	−3.7	−3.9	V	
			Full range	−3.3			
		R _L = 100 Ω	25°C	−2.5	−2.7		
			Full range	−2			
A _{VD}	Large-signal differential voltage amplification	V _O = ±2.8 V, R _L = 10 kΩ	25°C	15	80	V/mV	
			Full range	2			
		V _O = 0 to 2 V, R _L = 100 Ω	25°C	0.75	45		
			Full range	0.5			
		V _O = 0 to −2 V, R _L = 100 Ω	25°C	0.5	3		
			Full range	0.25			
r _i	Input resistance		25°C	10 ¹²		Ω	
c _i	Input capacitance		25°C	4		pF	
z _O	Open-loop output impedance	I _O = 0	25°C	280		Ω	
CMRR	Common-mode rejection ratio	V _{IC} = V _{ICRmin} , R _S = 50 Ω	25°C	65	82	dB	
			Full range	65			
k _{SVR}	Supply-voltage rejection ratio (ΔV _{CC±} /ΔV _{IO})	V _{CC±} = ±5 V to ±15 V, R _S = 50 Ω	25°C	75	93	dB	
			Full range	75			

† Full range is 0°C to 70°C.

NOTE 4: Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at $T_A = 150^\circ\text{C}$ extrapolated to $T_A = 25^\circ\text{C}$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.



electrical characteristics at specified free-air temperature, $V_{CC\pm} = \pm 5$ V (unless otherwise noted)
(continued)

PARAMETER	TEST CONDITIONS	$T_A^\dagger$	TLE2061C TLE2061AC TLE2061BC			UNIT
			MIN	TYP	MAX	
I_{CC} Supply current	$V_O = 0$, No load	25°C		280	325	μA
		Full range			350	
ΔI_{CC} Supply-current change over operating temperature range		Full range		29		μA

† Full range is 0°C to 70°C.

operating characteristics at specified free-air temperature, $V_{CC\pm} = \pm 5$ V

PARAMETER	TEST CONDITIONS	$T_A^\dagger$	TLE2061C TLE2061AC TLE2061BC			UNIT
			MIN	TYP	MAX	
SR Slew rate at unity gain (see Figure 1)	$R_L = 10$ k Ω , $C_L = 100$ pF	25°C	2.2	3.4		V/ μs
		Full range	2.1			
V_n Equivalent input noise voltage (see Figure 2)	$f = 10$ Hz, $R_S = 20$ Ω	25°C		59	100	nV/ $\sqrt{Hz}$
	$f = 1$ kHz, $R_S = 20$ Ω			43	60	
$V_{N(PP)}$ Peak-to-peak equivalent input noise voltage	$f = 0.1$ Hz to 10 Hz	25°C		1.1		μV
I_n Equivalent input noise current	$f = 1$ kHz	25°C		1		fA/ $\sqrt{Hz}$
THD Total harmonic distortion	$A_{VD} = 1$, $f = 10$ kHz, $V_{O(PP)} = 2$ V, $R_L = 10$ k Ω	25°C		0.025%		
B_1 Unity-gain bandwidth (see Figure 3)	$R_L = 10$ k Ω , $C_L = 100$ pF	25°C		1.8		MHz
	$R_L = 100$ Ω , $C_L = 100$ pF			1.3		
t_s Settling time	0.1%	25°C		5		μs
	0.01%			10		
B_{OM} Maximum output-swing bandwidth	$A_{VD} = 1$, $R_L = 10$ k Ω	25°C		140		kHz
ϕ_m Phase margin at unity gain (see Figure 3)	$R_L = 10$ k Ω , $C_L = 100$ pF	25°C		58°		
	$R_L = 100$ Ω , $C_L = 100$ pF			75°		

† Full range is 0°C to 70°C.

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electrical characteristics at specified free-air temperature, $V_{CC\pm} = \pm 15$ V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T _A [†]	TLE2061C TLE2061AC TLE2061BC			UNIT
				MIN	TYP	MAX	
V _{IO}	Input offset voltage	TLE2061C	25°C	0.6		3	mV
		TLE2061AC	Full range	3.9			
			25°C	0.5		1.5	
			Full range	2.5			
			25°C	0.3		0.5	
		TLE2061BC	Full range	1			
α _{VIO}	Temperature coefficient of input offset voltage	V _{IC} = 0, R _S = 50 kΩ	Full range	6		μV/°C	
Input offset voltage long-term drift (see Note 4)			25°C	0.04		μV/mo	
I _{IO}	Input offset current		25°C	2		pA	
			Full range	1		nA	
I _{IB}	Input bias current		25°C	4		pA	
			Full range	3		nA	
V _{ICR}	Common-mode input voltage range		25°C	−11 to 13	−12 to 16	V	
			Full range	−11 to 13		V	
V _{OM+}	Maximum positive peak output voltage swing		R _L = 10 kΩ	25°C	13.2	13.7	V
				Full range	13		
		R _L = 600 Ω	25°C	12.5	13.2		
			Full range	12			
V _{OM−}	Maximum negative peak output voltage swing	R _L = 10 kΩ	25°C	−13.2	−13.7	V	
			Full range	−13			
		R _L = 600 Ω	25°C	−12.5	−13		
			Full range	−12			
A _{VD}	Large-signal differential voltage amplification	V _O = ±10 V, R _L = 10 kΩ	25°C	30	230	V/mV	
			Full range	20			
		V _O = 0 to 8 V, R _L = 600 Ω	25°C	25	100		
			Full range	10			
		V _O = 0 to −8 V, R _L = 600 Ω	25°C	3	25		
			Full range	1			
r _i	Input resistance		25°C	10 ¹²		Ω	
c _i	Input capacitance		25°C	4		pF	
z ₀	Open-loop output impedance	I _O = 0	25°C	280		Ω	
CMRR	Common-mode rejection ratio	V _{IC} = V _{ICRmin} , R _S = 50 Ω	25°C	72	90	dB	
			Full range	70			
k _{SVR}	Supply-voltage rejection ratio (ΔV _{CC±} /ΔV _{IO})	V _{CC±} = ±5 V to ±15 V, R _S = 50 kΩ	25°C	75	93	dB	
			Full range	75			

† Full range is 0°C to 70°C.

NOTE 4: Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at $T_A = 150^\circ\text{C}$ extrapolated to $T_A = 25^\circ\text{C}$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.



electrical characteristics at specified free-air temperature, $V_{CC\pm} = \pm 15$ V (unless otherwise noted) (continued)

PARAMETER	TEST CONDITIONS	$T_A^\dagger$	TLE2061C TLE2061AC TLE2061BC			UNIT
			MIN	TYP	MAX	
I_{CC} Supply current	$V_O = 0$, No load	25°C		290	350	μA
		Full range			375	
ΔI_{CC} Supply-current change over operating temperature range		Full range		34		μA

† Full range is 0°C to 70°C.

operating characteristics at specified free-air temperature, $V_{CC\pm} = \pm 15$ V

PARAMETER	TEST CONDITIONS	$T_A^\dagger$	TLE2061C TLE2061AC TLE2061BC			UNIT
			MIN	TYP	MAX	
SR Slew rate at unity gain (see Figure 1)	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$	25°C	2.6	3.4		$V/\mu s$
		Full range	2.5			
V_n Equivalent input noise voltage (see Figure 2)	$f = 10\text{ Hz}$, $R_S = 20\text{ }\Omega$	25°C		70	100	$nV/\sqrt{Hz}$
	$f = 1\text{ kHz}$, $R_S = 20\text{ }\Omega$			40	60	
$V_{N(PP)}$ Peak-to-peak equivalent input noise voltage	$f = 0.1\text{ Hz to }10\text{ Hz}$	25°C		1.1		μV
I_n Equivalent input noise current	$f = 1\text{ kHz}$	25°C		1.1		$fA/\sqrt{Hz}$
THD Total harmonic distortion	$A_{VD} = 2$, $f = 10\text{ kHz}$, $V_{O(PP)} = 2\text{ V}$, $R_L = 10\text{ k}\Omega$	25°C		0.025%		
B_1 Unity-gain bandwidth (see Figure 3)	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$	25°C		2		MHz
	$R_L = 600\text{ }\Omega$, $C_L = 100\text{ pF}$			1.5		
t_s Settling time	0.1%	25°C		5		μs
	0.01%			10		
B_{OM} Maximum output-swing bandwidth	$A_{VD} = 1$, $R_L = 10\text{ k}\Omega$	25°C		40		kHz
ϕ_m Phase margin at unity gain (see Figure 3)	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$	25°C		60°		
	$R_L = 600\text{ }\Omega$, $C_L = 100\text{ pF}$			70°		

† Full range is 0°C to 70°C.

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electrical characteristics at specified free-air temperature, $V_{CC\pm} = \pm 5\text{ V}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T _A [†]	TLE2061I, TLE2061AI TLE2061BI			UNIT
				MIN	TYP	MAX	
V _{IO}	Input offset voltage	V _{IC} = 0, R _S = 50 Ω	25°C	0.8		3.1	mV
			Full range	4.4			
			25°C	0.6		2.6	
			Full range	3.9			
			25°C	0.5		1.9	
			Full range	2.7			
α _{VIO}	Temperature coefficient of input offset voltage		Full range	6		μV/°C	
Input offset voltage long-term drift (see Note 4)			25°C	0.04		μV/mo	
I _{IO}	Input offset current		25°C	1		pA	
			Full range	2		nA	
I _{IB}	Input bias current		25°C	3		pA	
			Full range	4		nA	
V _{ICR}	Common-mode input voltage range	25°C	–1.6 to 4	–2 to 6	V		
		Full range	–1.6 to 4		V		
V _{OM+}	Maximum positive peak output voltage swing	R _L = 10 kΩ	25°C	3.5	3.7	V	
			Full range	3.1			
		R _L = 100 Ω	25°C	2.5	3.1		
			Full range	2			
V _{OM–}	Maximum negative peak output voltage swing	R _L = 10 kΩ	25°C	–3.7	–3.9	V	
			Full range	–3.1			
		R _L = 100 Ω	25°C	–2.5	–2.7		
			Full range	–2			
A _{VD}	Large-signal differential voltage amplification	V _O = ±2.8 V, R _L = 10 kΩ	25°C	15	80	V/mV	
			Full range	2			
		V _O = 0 to 2 V, R _L = 100 Ω	25°C	0.75	45		
			Full range	0.5			
		V _O = 0 to –2 V, R _L = 100 Ω	25°C	0.5	3		
			Full range	0.25			
r _i	Input resistance		25°C	10 ¹²		Ω	
c _i	Input capacitance		25°C	4		pF	
z _O	Open-loop output impedance	I _O = 0	25°C	280		Ω	
CMRR	Common-mode rejection ratio	V _{IC} = V _{ICRmin} , R _S = 50 Ω	25°C	65	82	dB	
			Full range	65			
k _{SVR}	Supply-voltage rejection ratio (ΔV _{CC±} /ΔV _{IO})	V _{CC±} = ±5 V to ±15 V, R _S = 50 Ω	25°C	75	93	dB	
			Full range	65			
I _{CC}	Supply current	V _O = 0, No load	25°C	280	325	μA	
			Full range	350			
ΔI _{CC}	Supply-current change over operating temperature range		Full range	29		μA	

† Full range is -40°C to 85°C .

NOTE 4: Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at $T_A = 150^\circ\text{C}$ extrapolated to $T_A = 25^\circ\text{C}$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.



operating characteristics at specified free-air temperature, $V_{CC\pm} = \pm 5\text{ V}$

PARAMETER	TEST CONDITIONS	$T_A^\dagger$	TLE2061I TLE2061AI TLE2061BI			UNIT
			MIN	TYP	MAX	
SR Slew rate at unity gain (see Figure 1)	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$	25°C	2.2	3.4		V/ μs
		Full range	1.7			
V_n Equivalent input noise voltage (see Figure 2)	$f = 10\text{ Hz}$, $R_S = 20\text{ }\Omega$	25°C		59	100	nV/ $\sqrt{\text{Hz}}$
	$f = 1\text{ kHz}$, $R_S = 20\text{ }\Omega$			43	60	
$V_{N(PP)}$ Peak-to-peak equivalent input noise voltage	$f = 0.1\text{ Hz to }10\text{ Hz}$	25°C		1.1		μV
I_n Equivalent input noise current	$f = 1\text{ kHz}$	25°C		1		fA/ $\sqrt{\text{Hz}}$
THD Total harmonic distortion	$A_{VD} = 2$, $f = 10\text{ kHz}$, $V_{O(PP)} = 2\text{ V}$, $R_L = 10\text{ k}\Omega$	25°C		0.025%		
B_1 Unity-gain bandwidth (see Figure 3)	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$	25°C		1.8		MHz
	$R_L = 100\text{ }\Omega$, $C_L = 100\text{ pF}$			1.3		
t_s Settling time	0.1%	25°C		5		μs
	0.01%			10		
B_{OM} Maximum output-swing bandwidth	$A_{VD} = 1$, $R_L = 10\text{ k}\Omega$	25°C		140		kHz
ϕ_m Phase margin at unity gain (see Figure 3)	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$	25°C		58°		
	$R_L = 100\text{ }\Omega$, $C_L = 100\text{ pF}$			75°		

† Full range is -40°C to 85°C .

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electrical characteristics at specified free-air temperature, $V_{CC\pm} = \pm 15$ V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T _A [†]	TLE2061I, TLE2061AI TLE2061BI			UNIT
				MIN	TYP	MAX	
V _{IO}	Input offset voltage	V _{IC} = 0, R _S = 50 Ω	25°C	0.6		3	mV
			Full range	4.3			
			25°C	0.5		1.5	
			Full range	2.9			
			25°C	0.3		0.5	
			Full range	1.3			
αV _{IO}	Temperature coefficient of input offset voltage		Full range	6			μV/°C
Input offset voltage long-term drift (see Note 4)			25°C	0.04			μV/mo
I _{IO}	Input offset current		25°C	2			pA
			Full range	3			nA
I _{IB}	Input bias current		25°C	4			pA
			Full range	5			nA
V _{ICR}	Common-mode input voltage range	25°C	–11 to 13	–12 to 16		V	
		Full range	–11 to 13			V	
V _{OM+}	Maximum positive peak output voltage swing	R _L = 10 kΩ	25°C	13.2	13.7	V	
			Full range	13			
		R _L = 600 Ω	25°C	12.5	13.2		
			Full range	12			
V _{OM–}	Maximum negative peak output voltage swing	R _L = 10 kΩ	25°C	–13.2	–13.7	V	
			Full range	–13			
		R _L = 600 Ω	25°C	–12.5	–13		
			Full range	–12			
A _{VD}	Large-signal differential voltage amplification	V _O = ±10 V, R _L = 10 kΩ	25°C	30	230	V/mV	
			Full range	20			
		V _O = 0 to 8 V, R _L = 600 Ω	25°C	25	100		
			Full range	10			
		V _O = 0 to –8 V, R _L = 600 Ω	25°C	3	25		
			Full range	1			
r _i	Input resistance		25°C	10 ¹²		Ω	
c _i	Input capacitance		25°C	4		pF	
z _O	Open-loop output impedance	I _O = 0	25°C	280		Ω	
CMRR	Common-mode rejection ratio	V _{IC} = V _{ICRmin} , R _S = 50 Ω	25°C	72	90	dB	
			Full range	65			
k _{SVR}	Supply-voltage rejection ratio (ΔV _{CC±} /ΔV _{IO})	V _{CC±} = ±5 V to ±15 V, R _S = 50 Ω	25°C	75	93	dB	
			Full range	65			
I _{CC}	Supply current	V _O = 0, No load	25°C	290	350	μA	
			Full range	375			
ΔI _{CC}	Supply-current change over operating temperature range		Full range	34		μA	

† Full range is –40°C to 85°C.

NOTE 4: Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at $T_A = 150^\circ C$ extrapolated to $T_A = 25^\circ C$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.



operating characteristics at specified free-air temperature, $V_{CC\pm} = \pm 15\text{ V}$

PARAMETER	TEST CONDITIONS	$T_A^\dagger$	TLE2061I TLE2061AI TLE2061BI			UNIT
			MIN	TYP	MAX	
SR Slew rate at unity gain (see Figure 1)	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$	25°C	2.6	3.4		V/μs
		Full range	2.1			
V_n Equivalent input noise voltage (see Figure 2)	$f = 10\text{ Hz}$, $R_S = 20\ \Omega$	25°C		70	100	nV/√Hz
	$f = 1\text{ kHz}$, $R_S = 20\ \Omega$			40	60	
$V_{N(PP)}$ Peak-to-peak equivalent input noise voltage	$f = 0.1\text{ Hz to }10\text{ Hz}$	25°C		1.1		μV
I_n Equivalent input noise current	$f = 1\text{ kHz}$	25°C		1.1		fA/√Hz
THD Total harmonic distortion	$A_{VD} = 2$, $f = 10\text{ kHz}$, $V_{O(PP)} = 2\text{ V}$, $R_L = 10\text{ k}\Omega$	25°C		0.025%		
B_1 Unity-gain bandwidth (see Figure 3)	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$	25°C		2		MHz
	$R_L = 600\ \Omega$, $C_L = 100\text{ pF}$			1.5		
t_s Settling time	0.1%	25°C		5		μs
	0.01%			10		
B_{OM} Maximum output-swing bandwidth	$A_{VD} = 1$, $R_L = 10\text{ k}\Omega$	25°C		40		kHz
ϕ_m Phase margin at unity gain (see Figure 3)	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$	25°C		60°		
	$R_L = 600\ \Omega$, $C_L = 100\text{ pF}$			70°		

[†] Full range is –40°C to 85°C.

TLE2061, TLE2061A, TLE2061B, TLE2061Y
EXCALIBUR JFET-INPUT HIGH-OUTPUT-DRIVE
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electrical characteristics at specified free-air temperature, $V_{CC\pm} = \pm 5$ V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T _A [†]	TLE2061M TLE2061AM TLE2061BM			UNIT
				MIN	TYP	MAX	
V _{IO}	Input offset voltage	TLE2061M	25°C	0.8	3.1	mV	
			Full range	6			
			TLE2061AM	25°C	0.6		2.6
				Full range	4.6		
			TLE2061BM	25°C	0.5		1.9
				Full range	3.1		
α _{VIO}	Temperature coefficient of input offset voltage	V _{IC} = 0, R _S = 50 Ω	Full range	6		μV/°C	
Input offset voltage long-term drift (see Note 4)			25°C	0.04		μV/mo	
I _{IO}	Input offset current		25°C	1		pA	
			Full range	15		nA	
I _{IB}	Input bias current		25°C	3		pA	
			Full range	30		nA	
V _{ICR}	Common-mode input voltage range			25°C	−1.6 to 4	−2 to 6	V
				Full range	−1.6 to 4		V
V _{OM+}	Maximum positive peak output voltage swing		R _L = 10 kΩ	25°C	3.5	3.7	V
				Full range	3		
			R _L = 600 Ω	25°C	2.5	3.6	
				Full range	2		
		R _L = 100 Ω	25°C	2.5	3.1		
			Full range	2			
V _{OM−}	Maximum negative peak output voltage swing	R _L = 10 kΩ	25°C	−3.5	−3.9	V	
			Full range	−3			
		FK and JG packages	R _L = 600 Ω	25°C	−2.5		−3.5
			Full range	−2			
		D and P packages	R _L = 100 Ω	25°C	−2.5		−2.7
			Full range	−2			
A _{VD}	Large-signal differential voltage amplification	FK and JG packages	V _O = ±2.8 V, R _L = 10 kΩ	25°C	15	80	V/mV
				Full range	2		
			V _O = 0 to 2.5 V, R _L = 600 Ω	25°C	1	65	
				Full range	0.5		
			V _O = 0 to −2.5 V, R _L = 600 Ω	25°C	1	16	
				Full range	0.5		
		D and P packages	V _O = 0 to 2 V, R _L = 100 Ω	25°C	0.75	45	
				Full range	0.5		
			V _O = 0 to −2 V, R _L = 100 Ω	25°C	0.5	3	
				Full range	0.25		

† Full range is –55°C to 125°C.

NOTE 4: Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at $T_A = 150^\circ\text{C}$ extrapolated to $T_A = 25^\circ\text{C}$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.



electrical characteristics at specified free-air temperature, $V_{CC\pm} = \pm 5$ V (unless otherwise noted) (continued)

PARAMETER	TEST CONDITIONS	$T_A^\dagger$	TLE2061M TLE2061AM TLE2061BM			UNIT
			MIN	TYP	MAX	
r_i Input resistance		25°C		10 ¹²		Ω
c_i Input capacitance		25°C		4		pF
z_o Open-loop output impedance	$I_O = 0$	25°C		280		Ω
CMRR Common-mode rejection ratio	$V_{IC} = V_{ICRmin}$, $R_S = 50 \Omega$	25°C	65	82		dB
		Full range	60			
k_{SVR} Supply-voltage rejection ratio ($\Delta V_{CC\pm}/\Delta V_{IO}$)	$V_{CC\pm} = \pm 5$ V to ± 15 V, $R_S = 50 \Omega$	25°C	75	93		dB
		Full range	65			
I_{CC} Supply current	$V_O = 0$, No load	25°C		280	325	μA
		Full range			350	
ΔI_{CC} Supply-current change over operating temperature range		Full range		39		μA

[†] Full range is -55°C to 125°C .

operating characteristics at specified free-air temperature, $V_{CC\pm} = \pm 5$ V, $T_A = 25^\circ\text{C}$

PARAMETER	TEST CONDITIONS	TLE2061M TLE2061AM TLE2061BM			UNIT
		MIN	TYP	MAX	
SR Slew rate at unity gain (see Figure 1)	$R_L = 10 \text{ k}\Omega$, $C_L = 100 \text{ pF}$		3.4		V/ μs
V_n Equivalent input noise voltage (see Figure 2)	$f = 10 \text{ Hz}$, $R_S = 20 \Omega$		59		$\text{nV}/\sqrt{\text{Hz}}$
	$f = 1 \text{ kHz}$, $R_S = 20 \Omega$		43		
$V_{N(PP)}$ Peak-to-peak equivalent input noise voltage	$f = 0.1 \text{ Hz to } 10 \text{ Hz}$		1.1		μV
I_n Equivalent input noise current	$f = 1 \text{ kHz}$		1		$\text{fA}/\sqrt{\text{Hz}}$
THD Total harmonic distortion	$A_{VD} = 2$, $f = 10 \text{ kHz}$, $V_{O(PP)} = 2 \text{ V}$, $R_L = 10 \text{ k}\Omega$		0.025%		
B_1 Unity-gain bandwidth (see Figure 3)	$R_L = 10 \text{ k}\Omega$, $C_L = 100 \text{ pF}$		1.8		MHz
	$R_L = 600 \Omega$, $C_L = 100 \text{ pF}$		1.3		
t_s Settling time	0.1%		5		μs
	0.01%		10		
B_{OM} Maximum output-swing bandwidth	$A_{VD} = 1$, $R_L = 10 \text{ k}\Omega$		140		kHz
ϕ_m Phase margin at unity gain (see Figure 3)	$R_L = 10 \text{ k}\Omega$, $C_L = 100 \text{ pF}$		58°		
	$R_L = 600 \Omega$, $C_L = 100 \text{ pF}$		75°		

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electrical characteristics at specified free-air temperature, $V_{CC\pm} = \pm 15$ V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T _A [†]	TLE2061M, TLE2061AM TLE2061BM			UNIT
				MIN	TYP	MAX	
V _{IO}	Input offset voltage	V _{IC} = 0, R _S = 50 Ω	25°C	0.6		3	mV
			Full range	6			
			25°C	0.5		1.5	
			Full range	3.6			
			25°C	0.3		0.5	
			Full range	1.7			
α _{VIO}	Temperature coefficient of input offset voltage		Full range	6			μV/°C
Input offset voltage long-term drift (see Note 4)				25°C	0.04		μV/mo
I _{IO}	Input offset current			25°C	2		pA
				Full range	20		nA
I _{IB}	Input bias current			25°C	4		pA
				Full range	40		nA
V _{ICR}	Common-mode input voltage range	25°C	–11 to 13	–12 to 16	V		
		Full range	–11 to 13		V		
V _{OM+}	Maximum positive peak output voltage swing	R _L = 10 kΩ	25°C	13	13.7	V	
			Full range	12.5			
		R _L = 600 Ω	25°C	12.5	13.2		
			Full range	12			
V _{OM–}	Maximum negative peak output voltage swing	R _L = 10 kΩ	25°C	–13	–13.7	V	
			Full range	–12.5			
		R _L = 600 Ω	25°C	–12.5	–13		
			Full range	–12			
A _{VD}	Large-signal differential voltage amplification	V _O = ±10 V, R _L = 10 kΩ	25°C	30	230	V/mV	
			Full range	20			
		V _O = 0 to 8 V, R _L = 600 Ω	25°C	25	100		
			Full range	7			
		V _O = 0 to –8 V, R _L = 600 Ω	25°C	3	25		
			Full range	1			
r _i	Input resistance		25°C	10 ¹²		Ω	
c _i	Input capacitance		25°C	4		pF	
z _O	Open-loop output impedance	I _O = 0	25°C	280		Ω	
CMRR	Common-mode rejection ratio	V _{IC} = V _{ICRmin} , R _S = 50 Ω	25°C	72	90	dB	
			Full range	65			
k _{SVR}	Supply-voltage rejection ratio (ΔV _{CC±} /ΔV _{IO})	V _{CC±} = ±5 V to ±15 V, R _S = 50 Ω	25°C	75	93	dB	
			Full range	65			
I _{CC}	Supply current	V _O = 0, No load	25°C	290	350	μA	
			Full range	375			
ΔI _{CC}	Supply-current change over operating temperature range		Full range	46		μA	

† Full range is –55°C to 125°C.

NOTE 4: Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at $T_A = 150^\circ C$ extrapolated to $T_A = 25^\circ C$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.



operating characteristics at specified free-air temperature, $V_{CC\pm} = \pm 15\text{ V}$

PARAMETER	TEST CONDITIONS	$T_A^\dagger$	TLE2061M TLE2061AM TLE2061BM			UNIT
			MIN	TYP	MAX	
SR Slew rate at unity gain (see Figure 1)	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$	25°C	2	3.4		V/μs
		Full range	1.8			
V_n Equivalent input noise voltage (see Figure 2)	$f = 10\text{ Hz}$, $R_S = 20\text{ }\Omega$	25°C		70		nV/√Hz
	$f = 1\text{ kHz}$, $R_S = 20\text{ }\Omega$	25°C		40		
$V_{N(PP)}$ Peak-to-peak equivalent input noise voltage	$f = 0.1\text{ Hz to }10\text{ Hz}$	25°C		1.1		μV
I_n Equivalent input noise current	$f = 1\text{ kHz}$	25°C		1.1		fA/√Hz
THD Total harmonic distortion	$A_{VD} = 2$, $f = 10\text{ kHz}$, $V_{O(PP)} = 2\text{ V}$, $R_L = 10\text{ k}\Omega$	25°C		0.025%		
B_1 Unity-gain bandwidth (see Figure 3)	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$	25°C		2		MHz
	$R_L = 600\text{ }\Omega$, $C_L = 100\text{ pF}$	25°C		1.5		
t_s Settling time	0.1%	25°C		5		μs
	0.01%	25°C		10		
B_{OM} Maximum output-swing bandwidth	$A_{VD} = 1$, $R_L = 10\text{ k}\Omega$	25°C		40		kHz
ϕ_m Phase margin at unity gain (see Figure 3)	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$	25°C		60°		
	$R_L = 600\text{ }\Omega$, $C_L = 100\text{ pF}$	25°C		70°		

[†] Full range is –55°C to 125°C.

TLE2061, TLE2061A, TLE2061B, TLE2061Y
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electrical characteristics at $V_{CC\pm} = \pm 15\text{ V}$, $T_A = 25^\circ\text{C}$ (unless otherwise noted)

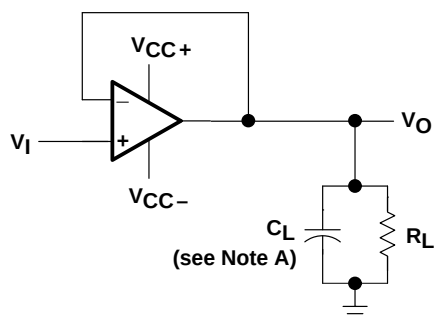
PARAMETER	TEST CONDITIONS	TLE2061Y			UNIT
		MIN	TYP	MAX	
V_{IO} Input offset voltage	$V_{IC} = 0$, $R_S = 50\ \Omega$		0.6	3	mV
αV_{IO} Input offset voltage long-term drift (see Note 4)			0.04		$\mu\text{V}/\text{mo}$
I_{IO} Input offset current			2		pA
I_{IB} Input bias current			4		pA
V_{ICR} Common-mode input voltage range		–11 to 13	–12 to 16		V
V_{OM+} Maximum positive peak output voltage swing	$R_L = 10\text{ k}\Omega$	13.2	13.7		V
	$R_L = 600\ \Omega$	12.5	13.2		
V_{OM-} Maximum negative peak output voltage swing	$R_L = 10\text{ k}\Omega$	–13.2	–13.7		V
	$R_L = 600\ \Omega$	–12.5	–13		
A_{VD} Large-signal differential voltage amplification	$V_O = \pm 10\text{ V}$, $R_L = 10\text{ k}\Omega$	30	230		V/mV
	$V_O = 0\text{ to }8\text{ V}$, $R_L = 600\ \Omega$	25	100		
	$V_O = 0\text{ to }-8\text{ V}$, $R_L = 600\ \Omega$	3	25		
r_i Input resistance			10^{12}		Ω
c_i Input capacitance			4		pF
z_o Open-loop output impedance	$I_O = 0$		280		Ω
CMRR Common-mode rejection ratio	$R_S = 50\ \Omega$, $V_{IC} = V_{ICR\text{min}}$	72	90		dB
k_{SVR} Supply-voltage rejection ratio ($\Delta V_{CC}/\Delta V_{IO}$)	$V_{CC\pm} = \pm 5\text{ V to } \pm 15\text{ V}$, $R_S = 50\ \Omega$	75	93		dB
I_{CC} Supply current	$V_O = 0$, No load		290	350	μA

NOTE 4: Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at $T_A = 150^\circ\text{C}$ extrapolated to $T_A = 25^\circ\text{C}$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.

operating characteristics at $V_{CC\pm} = \pm 15\text{ V}$, $T_A = 25^\circ\text{C}$

PARAMETER	TEST CONDITIONS	TLE2061Y			UNIT
		MIN	TYP	MAX	
SR Slew rate at unity gain	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$	2.6	3.4		$\text{V}/\mu\text{s}$
V_n Equivalent input noise voltage (see Figure 2)	$f = 10\text{ Hz}$, $R_S = 20\ \Omega$		70		$\text{nV}/\sqrt{\text{Hz}}$
	$f = 1\text{ kHz}$, $R_S = 20\ \Omega$		40		
$V_{N(PP)}$ Peak-to-peak equivalent input noise voltage	$f = 0.1\text{ Hz to }10\text{ Hz}$		1.1		μV
I_n Equivalent input noise current	$f = 1\text{ Hz}$		1.1		$\text{fA}/\sqrt{\text{Hz}}$
THD Total harmonic distortion	$A_{VD} = 2$, $f = 10\text{ kHz}$, $V_{O(PP)} = 2\text{ V}$, $R_L = 10\text{ k}\Omega$		0.025%		
B_1 Unity-gain bandwidth (see Figure 3)	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$		2		MHz
	$R_L = 600\ \Omega$, $C_L = 100\text{ pF}$		1.5		
t_s Settling time	0.1%		5		μs
	0.01%		10		
B_{OM} Maximum output-swing bandwidth	$A_{VD} = 1$, $R_L = 10\text{ k}\Omega$		40		kHz
ϕ_m Phase margin at unity gain (see Figure 3)	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$		60°		
	$R_L = 600\ \Omega$, $C_L = 100\text{ pF}$		70°		

PARAMETER MEASUREMENT INFORMATION



NOTE A: C_L includes fixture capacitance.

Figure 1. Slew-Rate Test Circuit

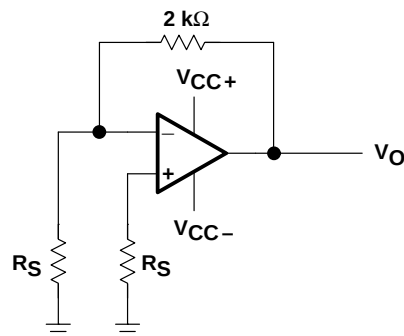
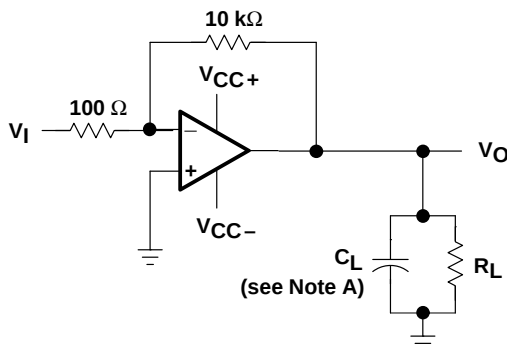


Figure 2. Noise-Voltage Test Circuit



NOTE A: C_L includes fixture capacitance.

Figure 3. Unity-Gain Bandwidth and Phase-Margin Test Circuit

typical values

Typical values presented in this data sheet represent the median (50% point) of device parametric performance.

input bias and offset current

At the picoampere bias-current level typical of the TLE2061, TLE2061A, and TLE2061B, accurate measurement of the bias current becomes difficult. Not only does this measurement require a picoammeter, but test socket leakages can easily exceed the actual device bias currents. To accurately measure these small currents, Texas Instruments uses a two-step process. The socket leakage is measured using picoammeters with bias voltages applied but with no device in the socket. The device is then inserted into the socket and a second test that measures both the socket leakage and the device input bias current is performed. The two measurements are then subtracted mathematically to determine the bias current of the device.

TYPICAL CHARACTERISTICS

Table of Graphs

			FIGURE
V_{IO}	Input offset voltage	Distribution	4
I_{IB}	Input bias current	vs Common-mode input voltage	5
		vs Free-air temperature	6
I_{IO}	Input offset current	vs Free-air temperature	6
V_{ICR}	Common-mode input voltage range limits	vs Free-air temperature	7
V_{OM}	Maximum peak output voltage	vs Output current	8, 9
		vs Supply voltage	10, 11, 12
$V_{O(PP)}$	Maximum peak-to-peak output voltage	vs Frequency	13, 14
A_{VD}	Large-signal differential voltage amplification	vs Frequency	15
		vs Free-air temperature	16
I_{OS}	Short-circuit output current	vs Time	17
		vs Free-air temperature	18
z_o	Output impedance	vs Frequency	19
CMRR	Common-mode rejection ratio	vs Frequency	20
I_{CC}	Supply current	vs Supply voltage	21
		vs Free-air temperature	22
	Pulse response	Small signal Large signal	23, 24 25, 26
	Noise voltage (referred to input)	0.1 to 10 Hz	27
V_n	Equivalent input noise voltage	vs Frequency	28
THD	Total harmonic distortion	vs Frequency	29, 30
B_1	Unity-gain bandwidth	vs Supply voltage	31
		vs Free-air temperature	32
ϕ_m	Phase margin	vs Supply voltage	33
		vs Load capacitance	34
		vs Free-air temperature	35
	Phase shift	vs Frequency	15

TYPICAL CHARACTERISTICS†

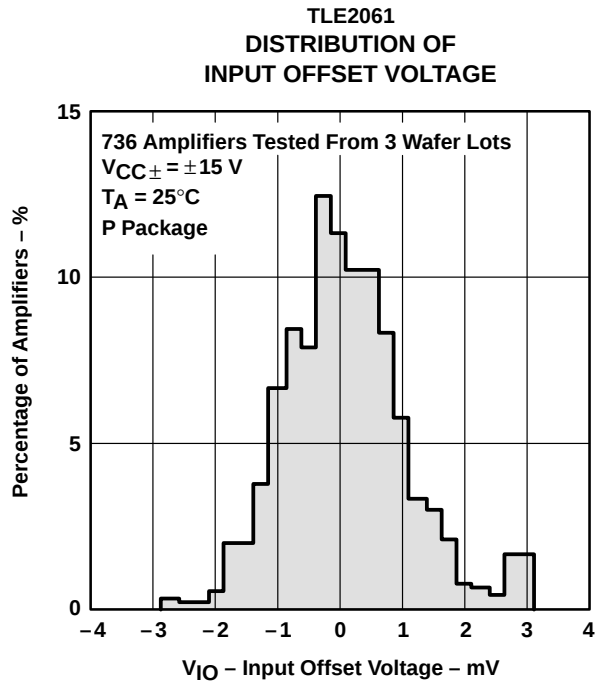


Figure 4

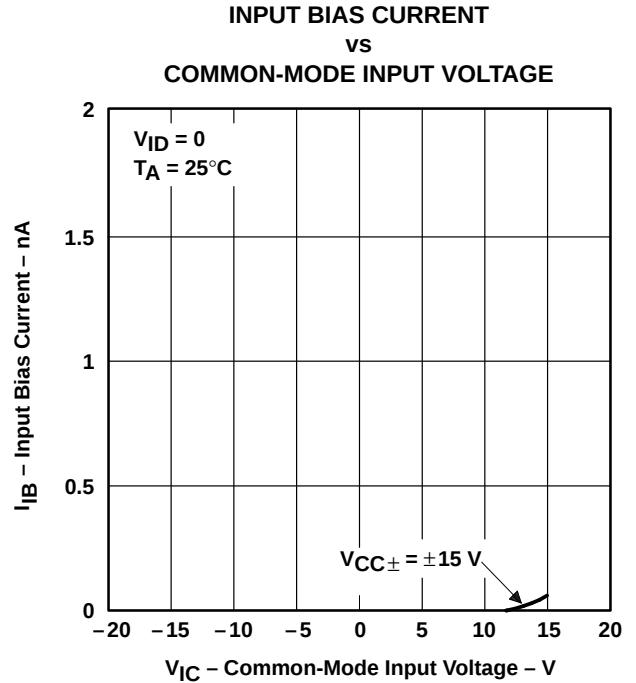


Figure 5

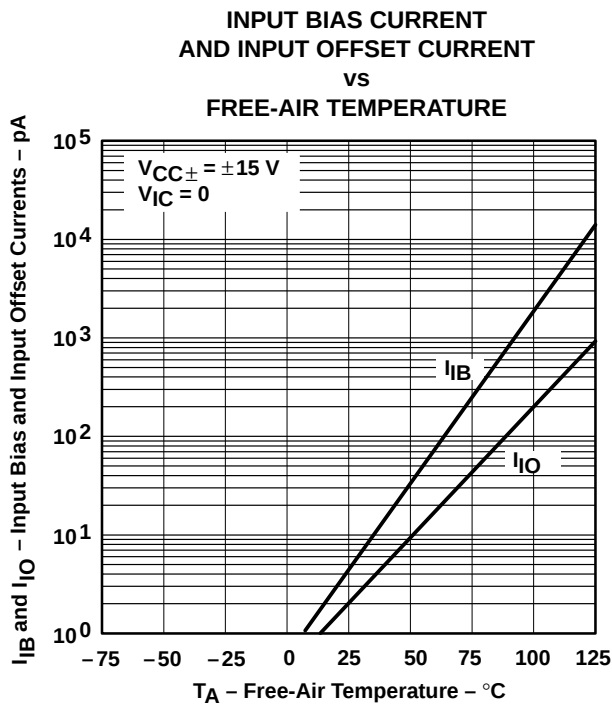


Figure 6

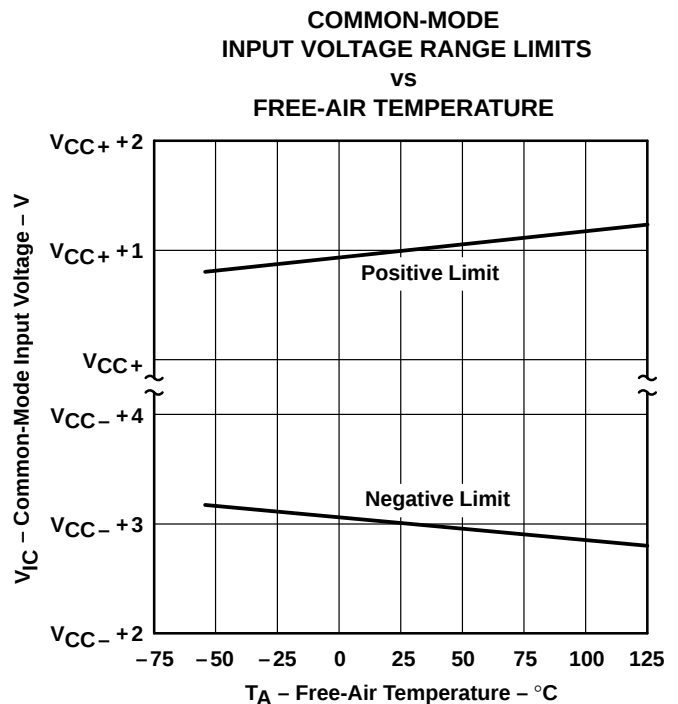


Figure 7

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS

MAXIMUM POSITIVE PEAK
OUTPUT VOLTAGE
vs
OUTPUT CURRENT

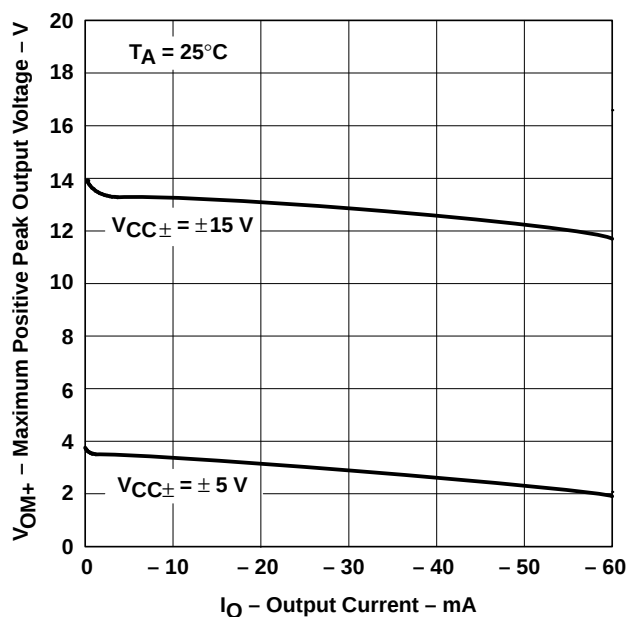


Figure 8

MAXIMUM NEGATIVE PEAK
OUTPUT VOLTAGE
vs
OUTPUT CURRENT

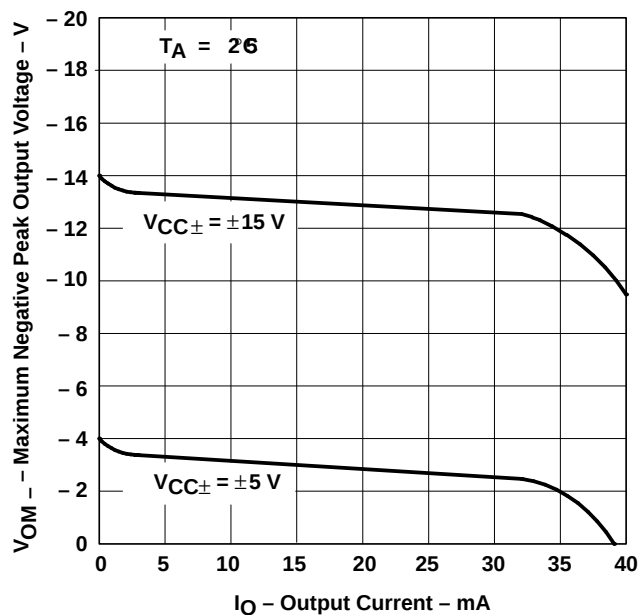


Figure 9

MAXIMUM PEAK OUTPUT VOLTAGE
vs
SUPPLY VOLTAGE

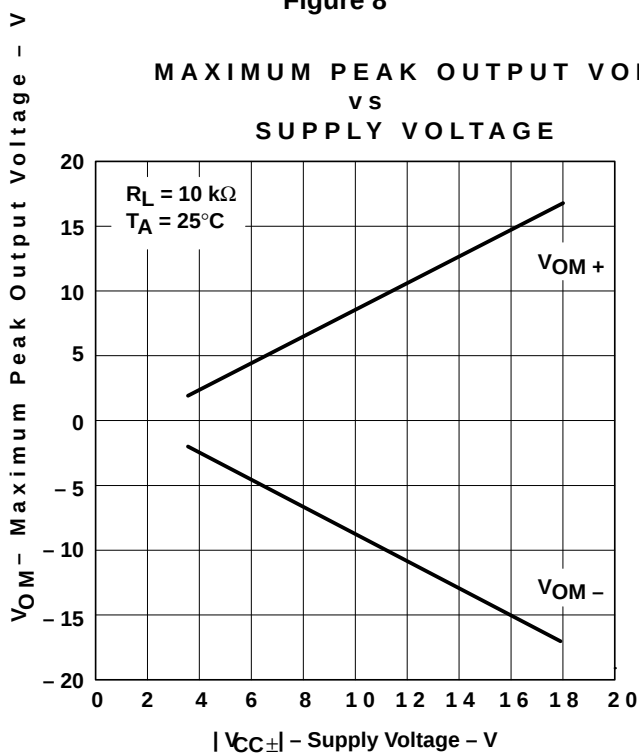


Figure 10

MAXIMUM PEAK OUTPUT VOLTAGE
vs
SUPPLY VOLTAGE

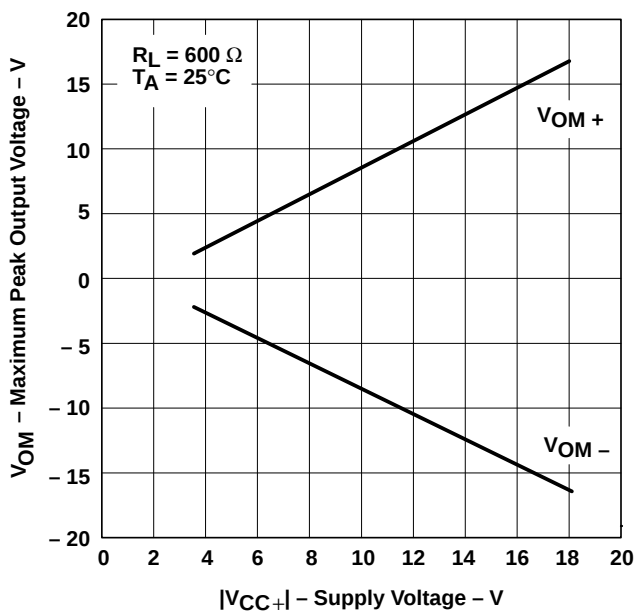


Figure 11

TYPICAL CHARACTERISTICS

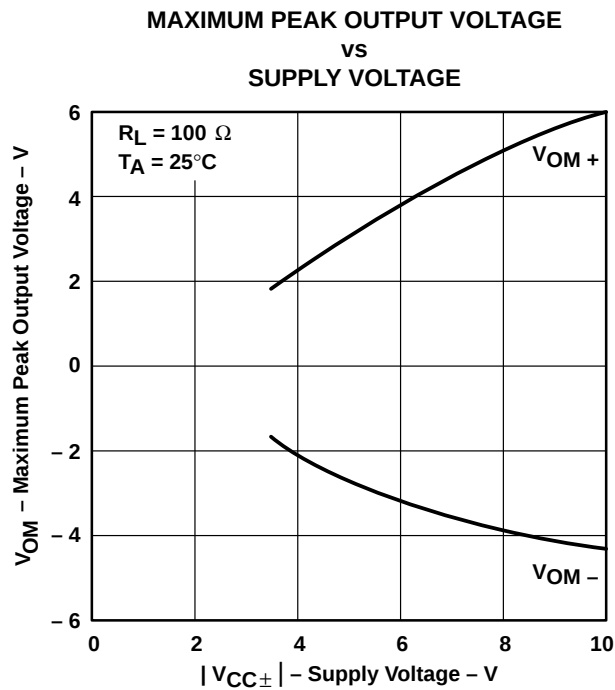


Figure 12

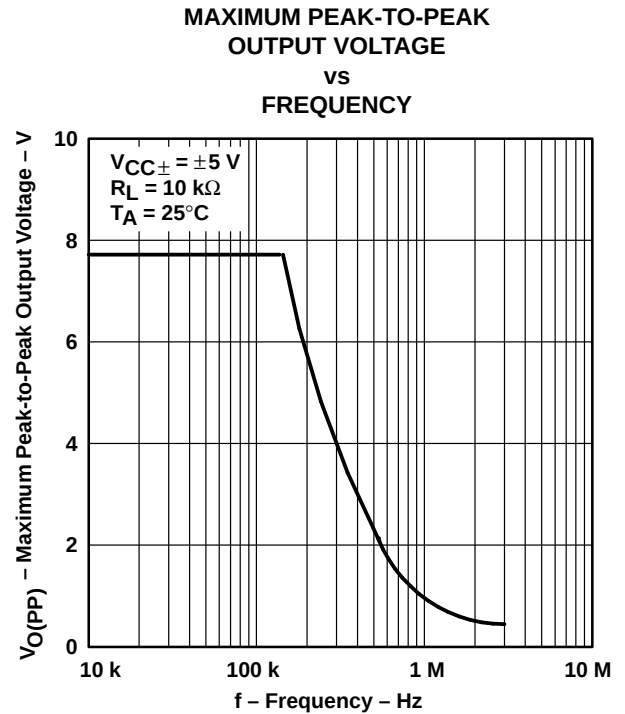


Figure 13

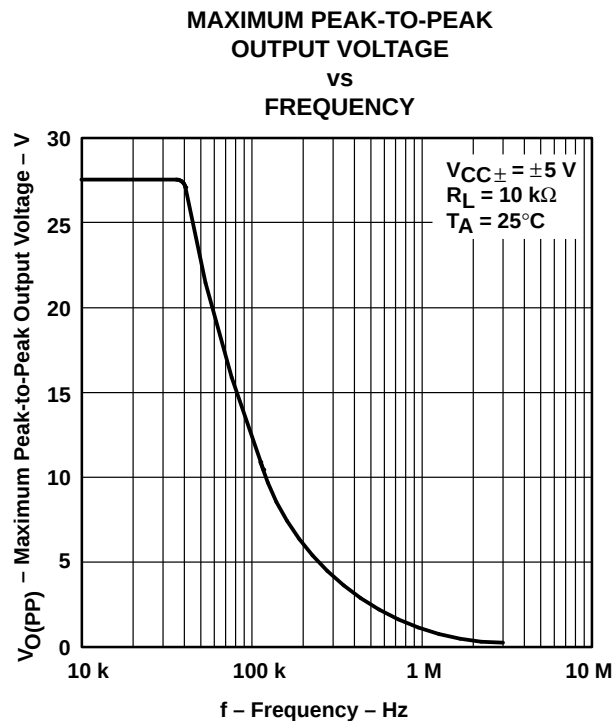


Figure 14

TYPICAL CHARACTERISTICS†

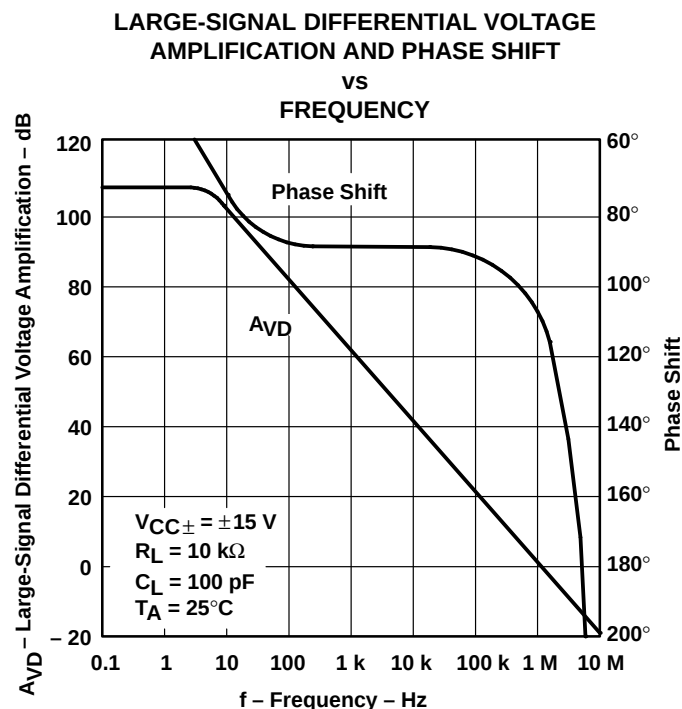


Figure 15

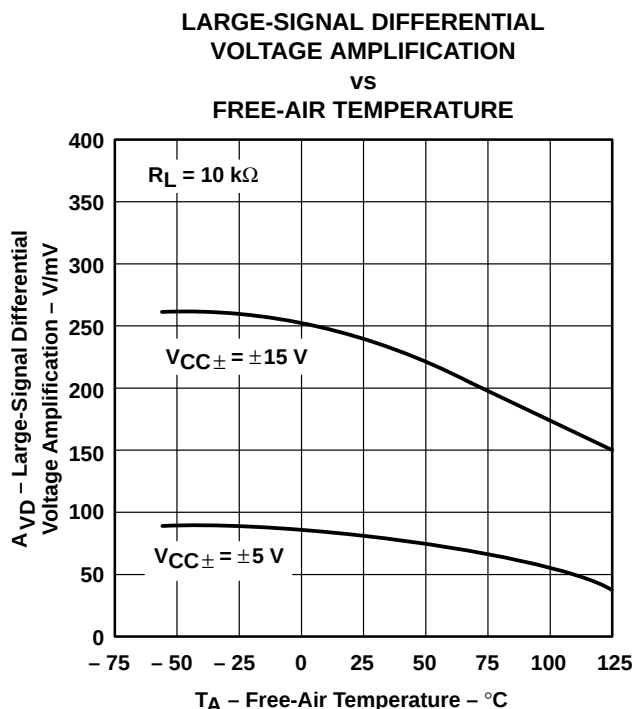


Figure 16

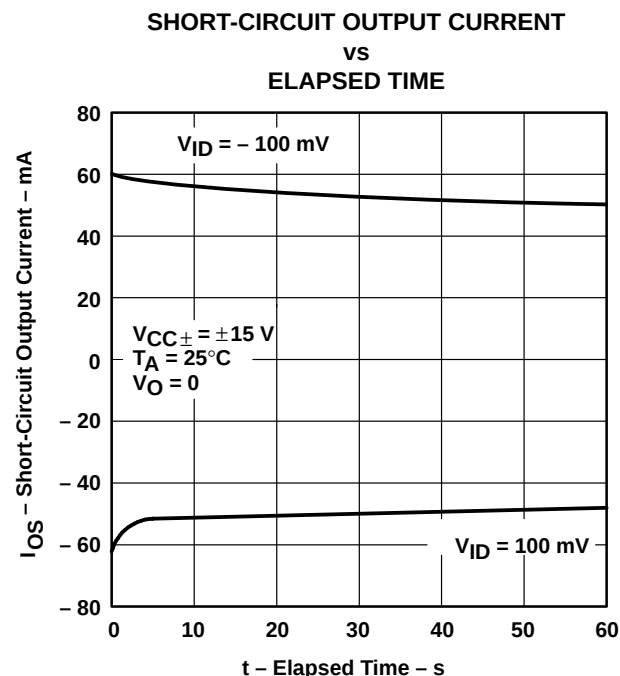


Figure 17

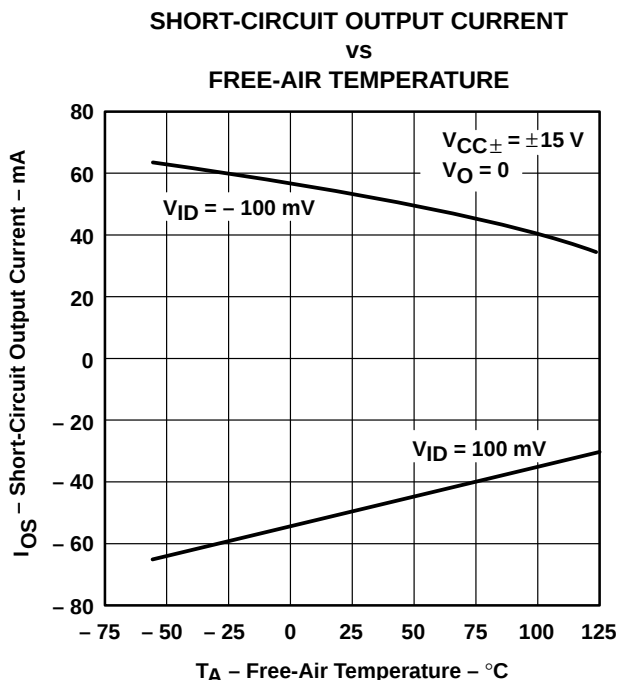
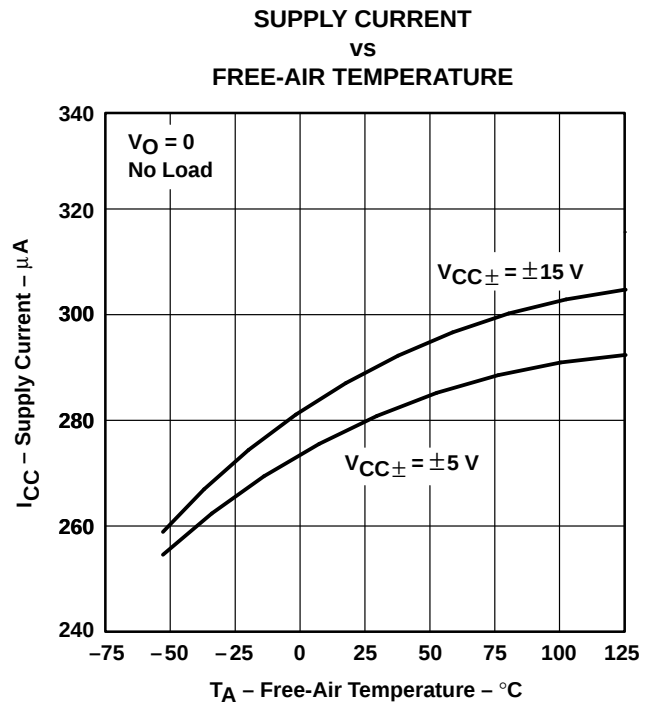
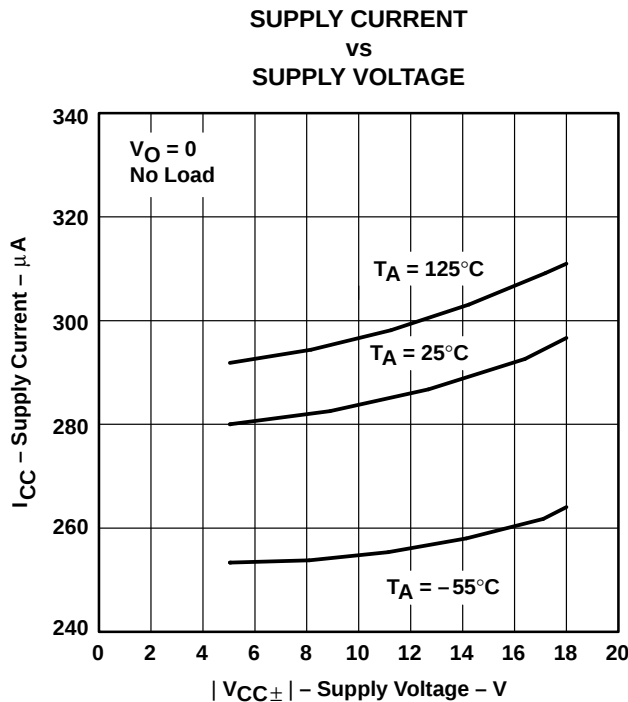
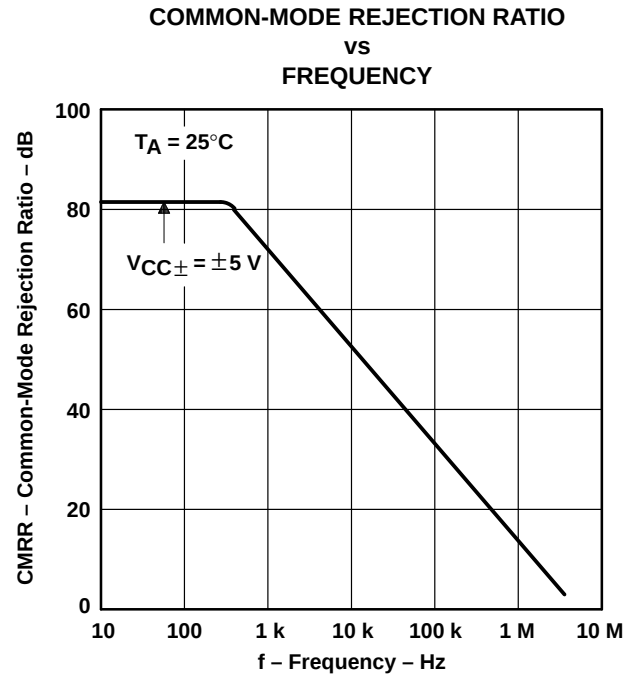
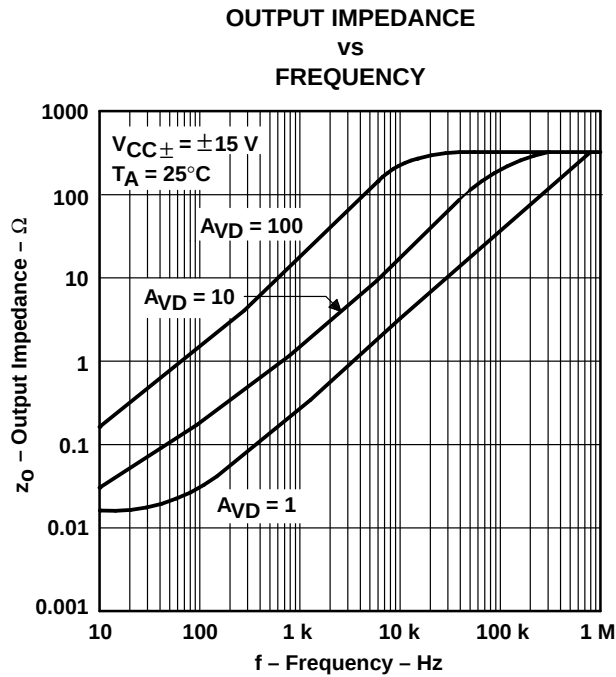


Figure 18

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS†



† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS

**VOLTAGE-FOLLOWER
 SMALL-SIGNAL
 PULSE RESPONSE**

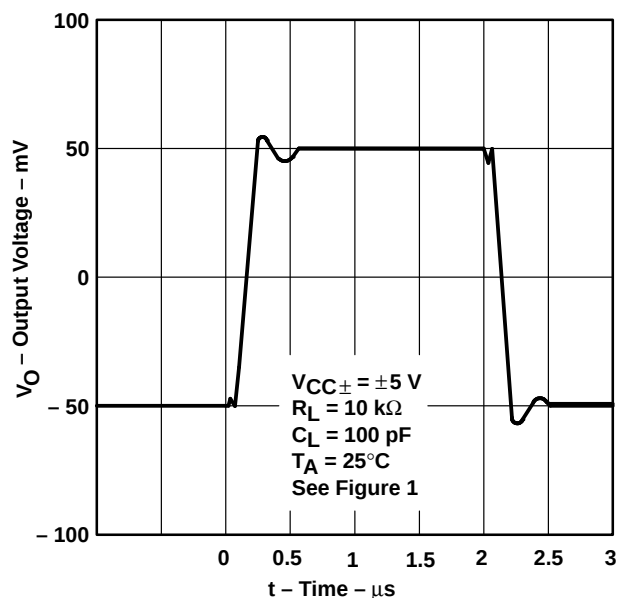


Figure 23

**VOLTAGE-FOLLOWER
 SMALL-SIGNAL
 PULSE RESPONSE**

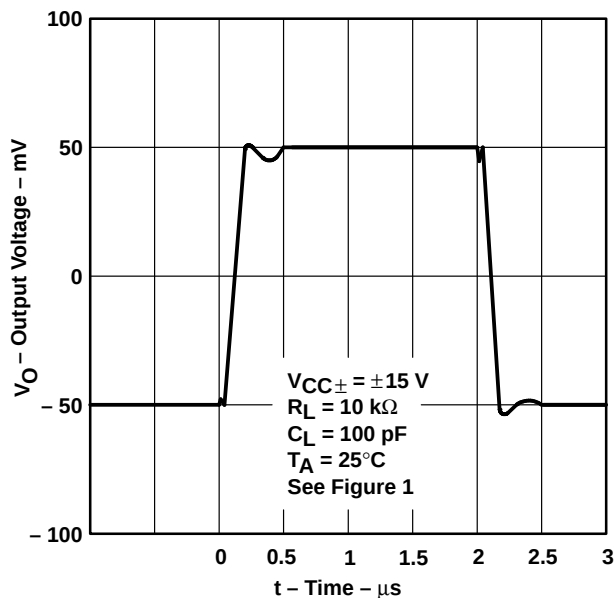


Figure 24

**VOLTAGE-FOLLOWER
 LARGE-SIGNAL
 PULSE RESPONSE**

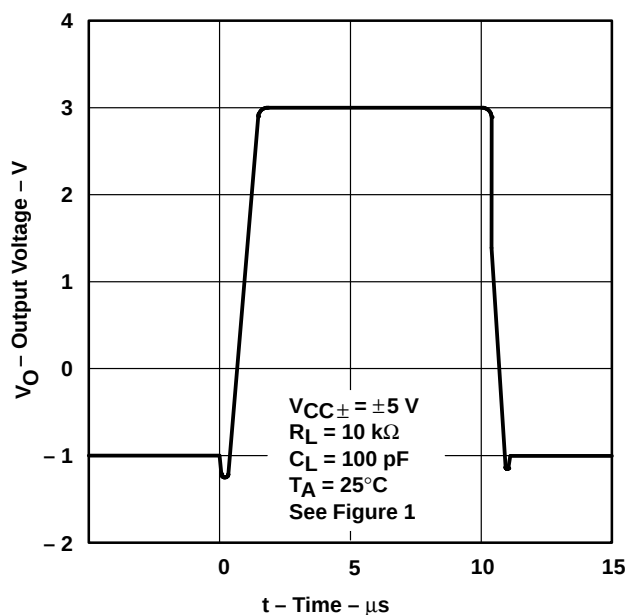


Figure 25

**VOLTAGE-FOLLOWER
 LARGE-SIGNAL
 PULSE RESPONSE**

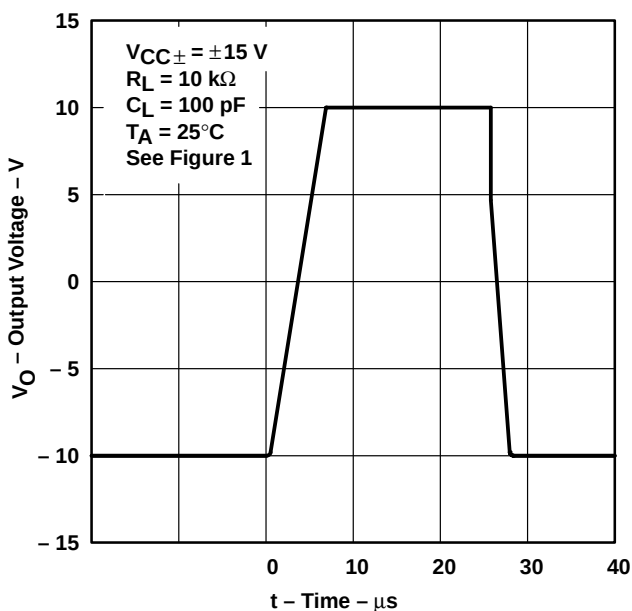


Figure 26

TYPICAL CHARACTERISTICS

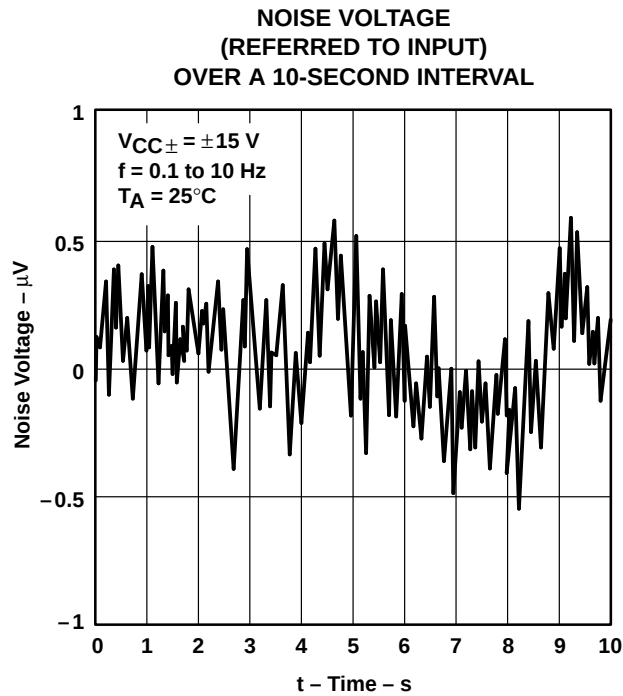


Figure 27

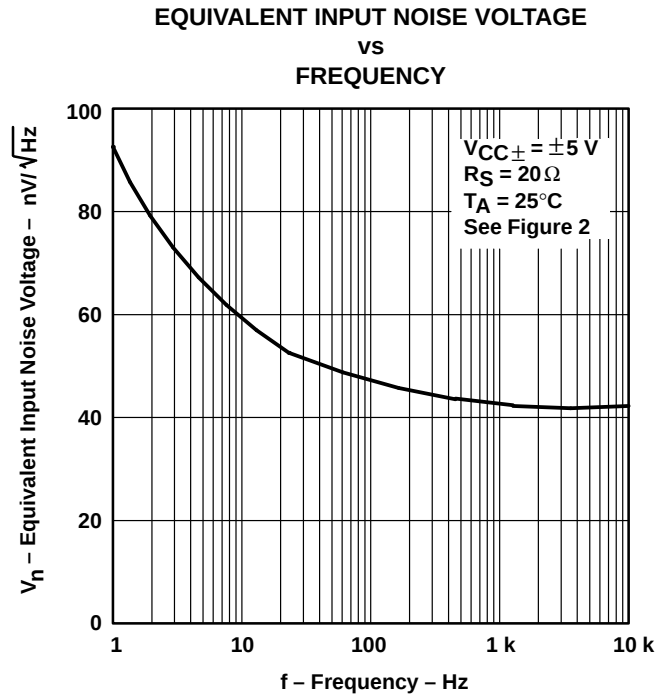


Figure 28

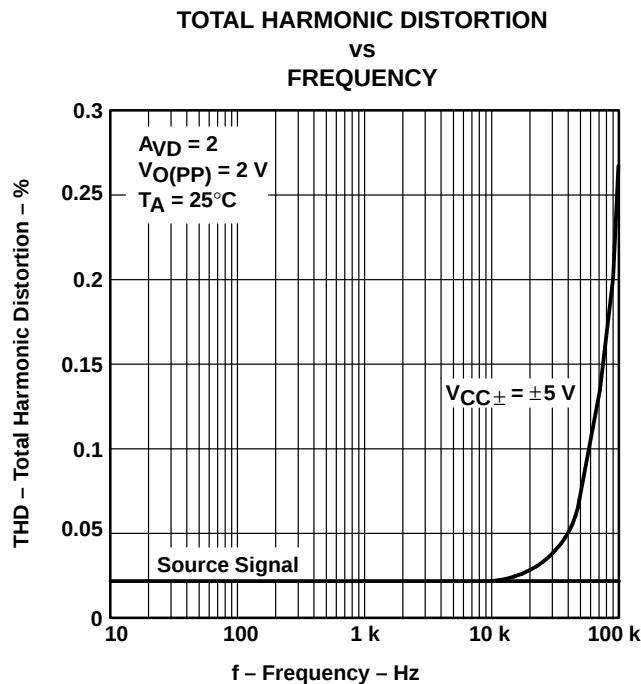


Figure 29

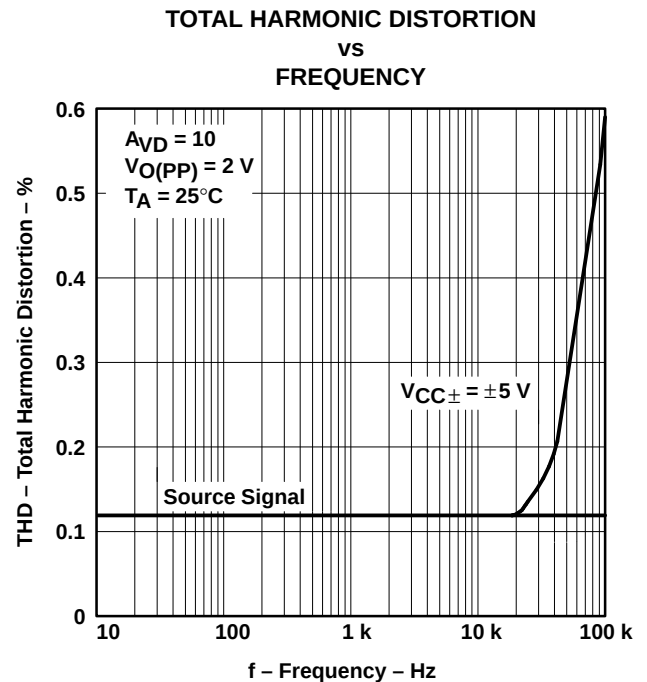


Figure 30

TYPICAL CHARACTERISTICS†

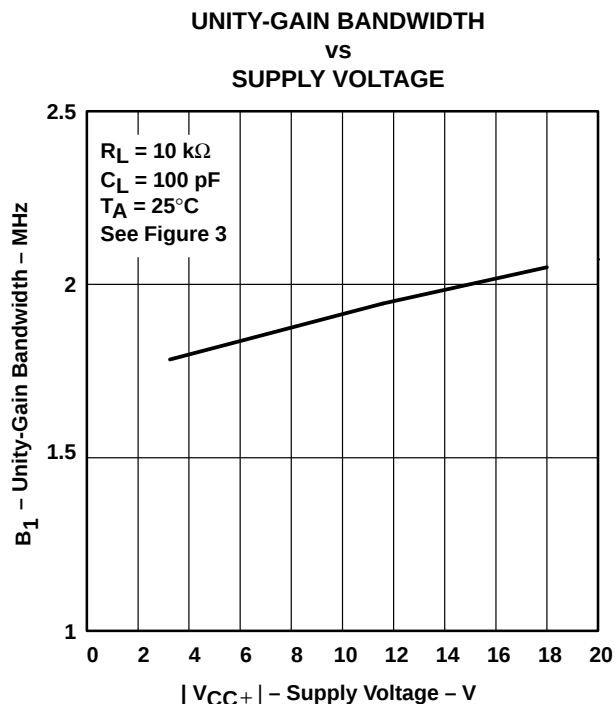


Figure 31

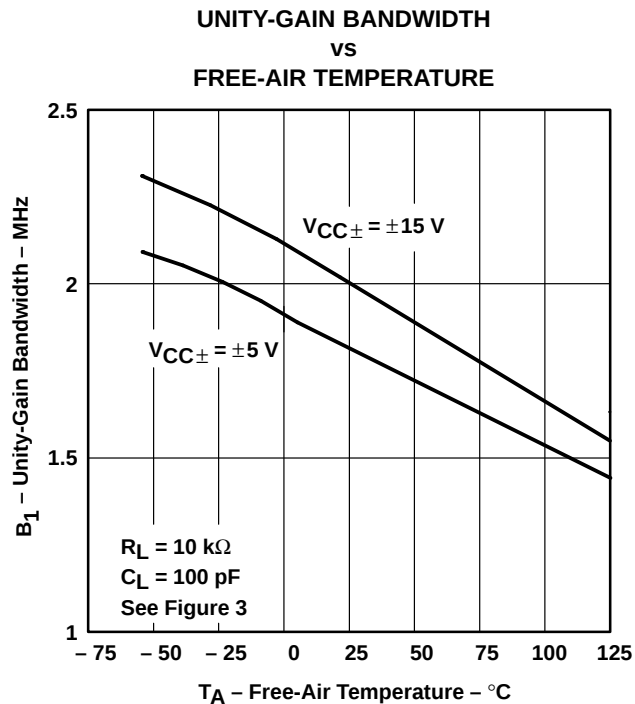


Figure 32

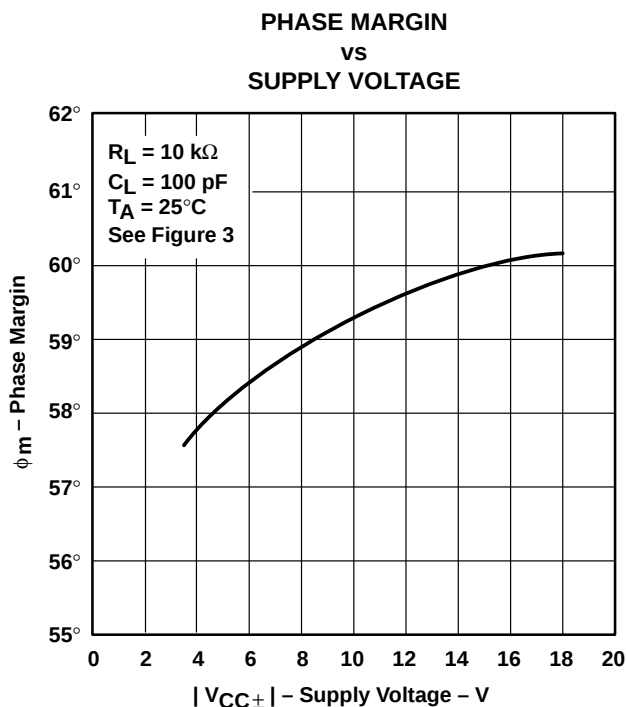


Figure 33

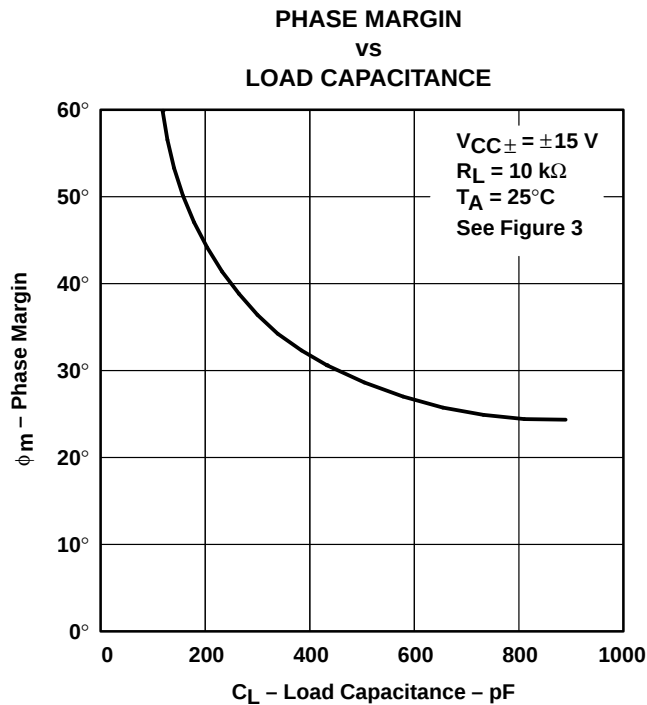
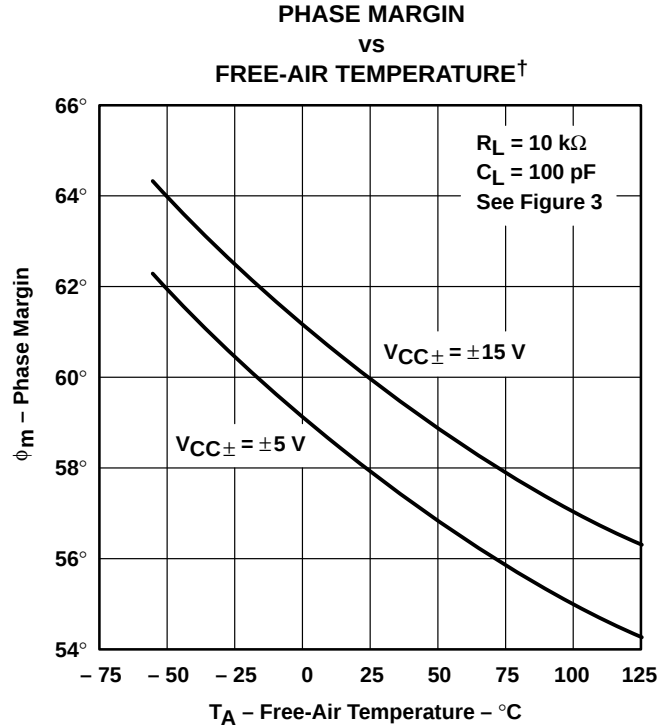


Figure 34

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS



† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

Figure 35

APPLICATION INFORMATION

macromodel information

Macromodel information provided is derived using Microsim *PSpice*™ and Microsim *Parts*™ model generation software. The Boyle macromodel (see Note 5) and subcircuit in Figure 36 are generated using the TLE2061 typical electrical and operating characteristics at 25°C. Using this information, output simulations of the following key parameters can be generated to a tolerance of 20% (in most cases):

- Maximum positive output voltage swing
- Maximum negative output voltage swing
- Slew rate
- Quiescent power dissipation
- Input bias current
- Open-loop voltage amplification
- Unity-gain frequency
- Common-mode rejection ratio
- Phase margin
- DC output resistance
- AC output resistance
- Short-circuit output current limit

NOTE 5: G. R. Boyle, B. M. Cohn, D. O. Pederson, and J. E. Solomon, "Macromodeling of Integrated Circuit Operational Amplifiers", *IEEE Journal of Solid-State Circuits*, SC-9, 353 (1974).

PSpice and *Parts* are trademarks of MicroSim Corporation.

Macromodels, simulation models, or other models provided by TI, directly or indirectly, are not warranted by TI as fully representing all of the specifications and operating characteristics of the semiconductor product to which the model relates.



TLE2061, TLE2061A, TLE2061B, TLE2061Y

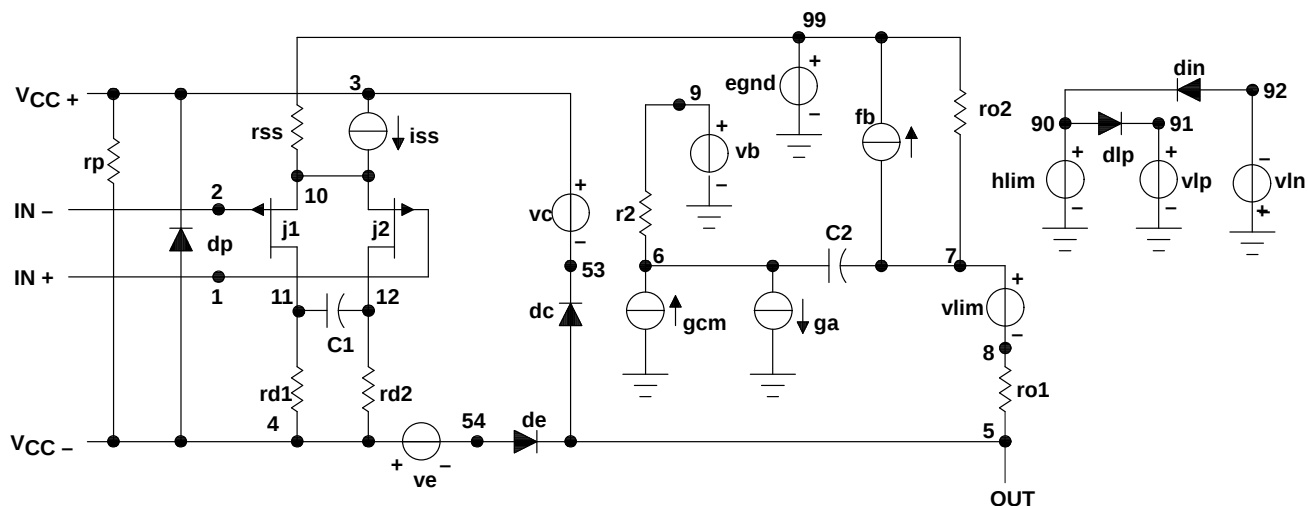
EXCALIBUR JFET-INPUT HIGH-OUTPUT-DRIVE

μPOWER OPERATIONAL AMPLIFIERS

SLOS045F – OCTOBER 1989 – REVISED SEPTEMBER 1996

APPLICATION INFORMATION

macromodel information (continued)



```
.subckt TLE2061 1 2 3 4 5
c1 11 12 1.457E-12
c2 6 7 15.00E-12
dc 5 53 dx
de 54 5 dx
dlp 90 91 dx
dln 92 90 dx
dp 4 3 dx
egnd 99 0 poly(2) (3,0) (4,0) 0 .5 .5
fb 7 99 poly(5) vb vc ve vlp vln 0 4.357E6 -4E6 4E6 4E6 -4E6
ga 6 0 11 12 188.5E-6
gcm 0 6 10 99 3.352E-9
iss 3 10 dc 51.00E-6
hlim 90 0 vlim 1K
j1 11 2 10 jx
j2 12 1 10 jx
r2 6 9 100.0E3
rd1 4 11 5.305E3
rd2 4 12 5.305E3
ro1 8 5 280
ro2 7 99 280
rp 3 4 113.2E3
rss 10 99 3.922E6
vb 9 0 dc 0
vc 3 53 dc 2
ve 54 4 dc 2
vlim 7 8 dc 0
vlp 91 0 dc 50
vln 0 92 dc 50
.model dx D(Is=800.0E-18)
.model jx PJF(Is=2.000E-12 Beta=423E-6 Vto=-1)
.ends
```

Figure 36. Boyle Macromodel and Subcircuit

APPLICATION INFORMATION

input characteristics

The TLE2061, TLE2061A, and TLE2061B are specified with a minimum and a maximum input voltage that if exceeded at either input could cause the device to malfunction. Because of the extremely high input impedance and resulting low bias current requirements, the TLE2061, TLE2061A, and TLE2061B are well suited for low-level signal processing; however, leakage currents on printed-circuit boards and sockets can easily exceed bias current requirements and cause degradation in system performance. It is good practice to include guard rings around inputs (see Figure 37). These guards should be driven from a low-impedance source at the same voltage level as the common-mode input.

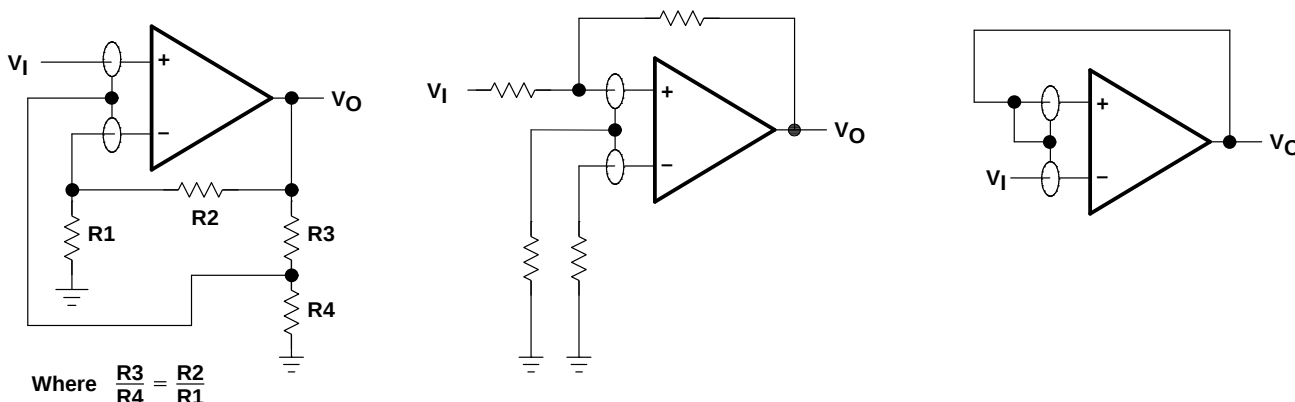


Figure 37. Use of Guard Rings

input offset voltage nulling

The TLE2061 series offers external null pins that can be used to further reduce the input offset voltage. The circuit of Figure 38 can be connected as shown if the feature is desired. When external nulling is not needed, the null pins may be left unconnected.

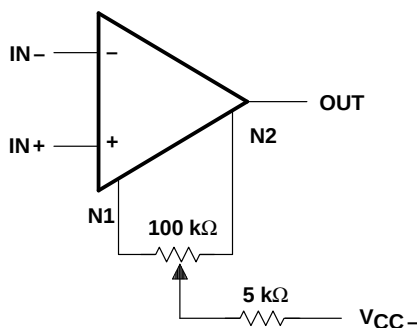


Figure 38. Input Offset Voltage Nulling

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